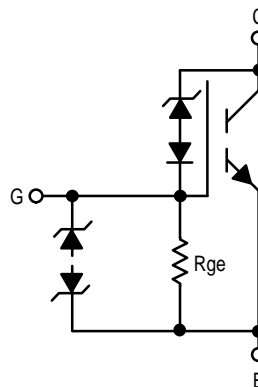


Advanced Information
SMARTDISCRETES™
Internally Clamped, N-Channel IGBT

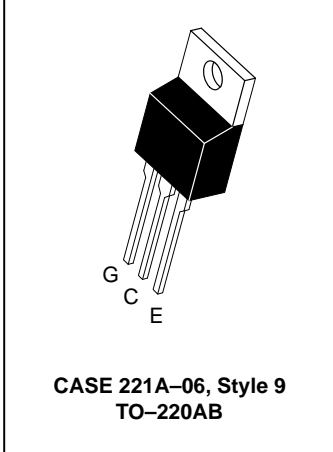
This Logic Level Insulated Gate Bipolar Transistor (IGBT) features Gate–Emitter ESD protection, Gate–Collector overvoltage protection from SMARTDISCRETES™ monolithic circuitry for usage as an **Ignition Coil Driver**.

- Temperature Compensated Gate–Drain Clamp Limits Stress Applied to Load
- Integrated ESD Diode Protection
- Low Threshold Voltage to Interface Power Loads to Logic or Microprocessors
- Low Saturation Voltage
- High Pulsed Current Capability



MGP20N35CL

**20 AMPERES
VOLTAGE CLAMPED
N-CHANNEL IGBT
V_{ce(on)} = 1.8 VOLTS
350 VOLTS (CLAMPED)**



MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V _{CES}	CLAMPED	V _{dc}
Collector–Gate Voltage	V _{CGR}	CLAMPED	V _{dc}
Gate–Emitter Voltage	V _{GE}	CLAMPED	V _{dc}
Collector Current — Continuous @ T _C = 25°C	I _C	20	A _{dc}
Reversed Collector Current – pulse width < 100 μs	I _{CR}	12	A _{pk}
Total Power Dissipation @ T _C = 25°C (TO-220)	P _D	150	Watts
Electrostatic Voltage — Gate–Emitter	ESD	3.5	kV
Operating and Storage Temperature Range	T _J , T _{stg}	–55 to 175	°C

THERMAL CHARACTERISTICS

Thermal Resistance — Junction to Case – (TO-220) — Junction to Ambient	R _{θJC} R _{θJA}	1.0 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	T _L	275	°C
Mounting Torque, 6–32 or M3 screw	10 lbf•in (1.13 N•m)		

UNCLAMPED INDUCTIVE SWITCHING CHARACTERISTICS

Single Pulse Collector–Emitter Avalanche Energy @ Starting T _J = 25°C @ Starting T _J = 150°C	E _{AS}	550 150	mJ
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This document contains information on a new product. Specifications and information herein are subject to change without notice.

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-to-Emitter Breakdown Voltage (I _{Clamp} = 10 mA, T _J = -40 to 150°C)	B _V CE _S	320	350	380	V _{dc}
Zero Gate Voltage Collector Current (V _{CE} = 250 V, V _{GE} = 0 V, T _J = 125°C) (V _{CE} = 15 V, V _{GE} = 0 V, T _J = 125°C)	I _{CES}	— —	— —	1.0 200	mA μA
Resistance Gate-Emitter (T _J = -40 to 150°C)	R _{GE}	10k	16k	30k	Ω
Gate-Emitter Breakdown Voltage (I _G = 2 mA)	B _V GES	11	13	15	± V
Collector-Emitter Reverse Leakage (V _{CE} = -15 V, T _J = -40 to 150°C)	I _{CES}	—	8	100	mA
Collector-Emitter Reversed Breakdown Voltage (I _E = 75 mA)	B _V CER	26	40	120	V

ON CHARACTERISTICS (1)

Gate Threshold Voltage (V _{CE} = V _{GE} , I _C = 1 mA) (V _{CE} = V _{GE} , I _C = 1 mA, T _J = 150°C)	V _{GE(th)}	1.0 0.75	1.7 —	2.4 1.8	V
Collector-Emitter On-Voltage (V _{GE} = 5 V, I _C = 5 A) (V _{GE} = 5 V, I _C = 10 A) (V _{GE} = 5 V, I _C = 10 A _{dc} , T _J = 150°C)	V _{CE(on)}	— — —	1.1 1.4 1.4	1.4 1.9 1.8	V
Forward Transconductance (V _{CE} > 50 V, I _C = 10 A)	g _{fs}	10	16	—	S

DYNAMIC CHARACTERISTICS

Input Capacitance	(V _{CE} = 25 V _{dc} , V _{GE} = 0 V _{dc} , f = 1.0 MHz)	C _{iss}	—	2800	—	pF
Output Capacitance		C _{oss}	—	200	—	
Transfer Capacitance		C _{r_{ss}}	—	25	—	

SWITCHING CHARACTERISTICS (1)

Total Gate Charge	(V _{CC} = 280 V, I _C = 20 A, V _{GE} = 5 V)	Q _g	—	45	80	nC
Gate-Emitter Charge		Q _{gs}	—	8.0	—	
Gate-Collector Charge		Q _{gd}	—	20	—	
Turn-Off Delay Time	(V _{CC} = 320 V, I _C = 20 A, L = 200 μH, R _G = 1 KΩ)	t _{d(off)}	—	TBD	TBD	μs
Fall Time		t _f	—	TBD	TBD	
Turn-On Delay Time	(V _{CC} = 14 V, I _C = 20 A, L = 200 μH, R _G = 1 KΩ)	t _{d(on)}	—	TBD	TBD	μs
Rise Time		t _r	—	TBD	TBD	

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

TYPICAL ELECTRICAL CHARACTERISTICS

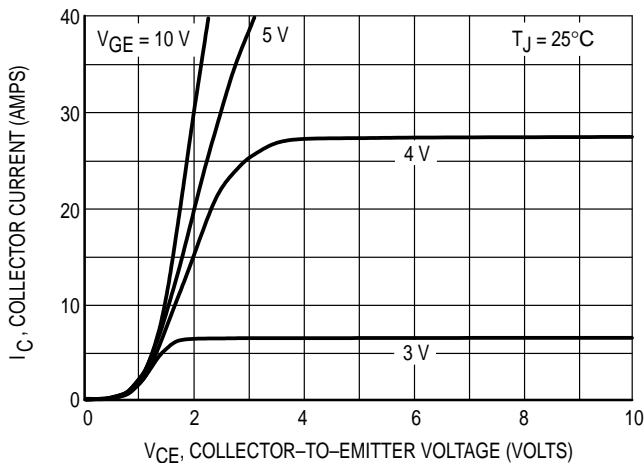


Figure 1. Output Characteristics, $T_J = 25^\circ\text{C}$

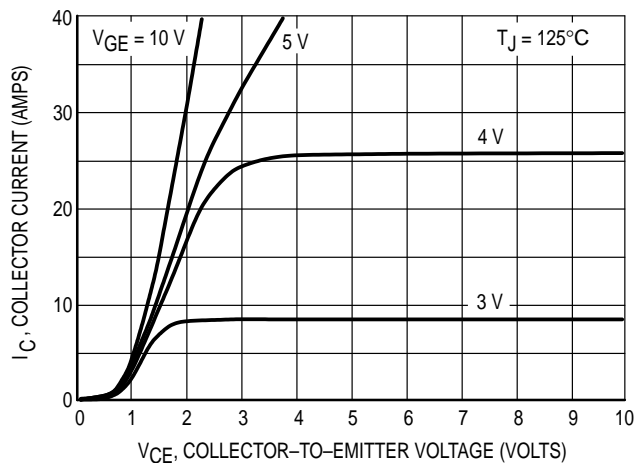


Figure 2. Output Characteristics, $T_J = 125^\circ\text{C}$

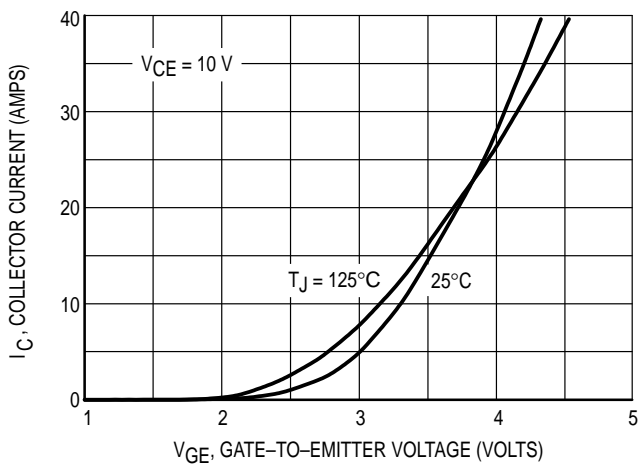


Figure 3. Transfer Characteristics

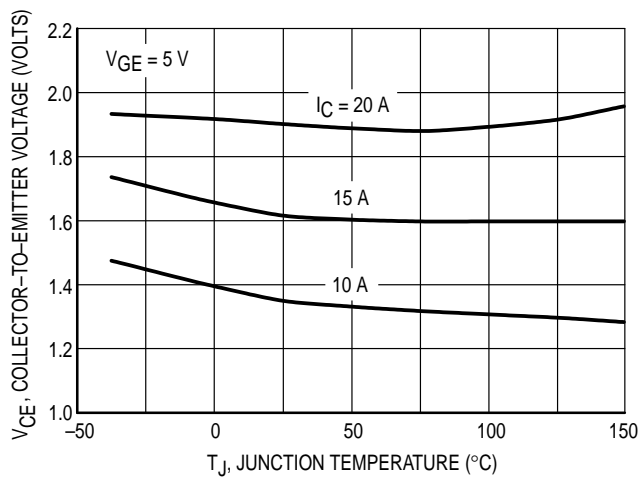


Figure 4. Collector-to-Emitter Saturation Voltage versus Junction Temperature

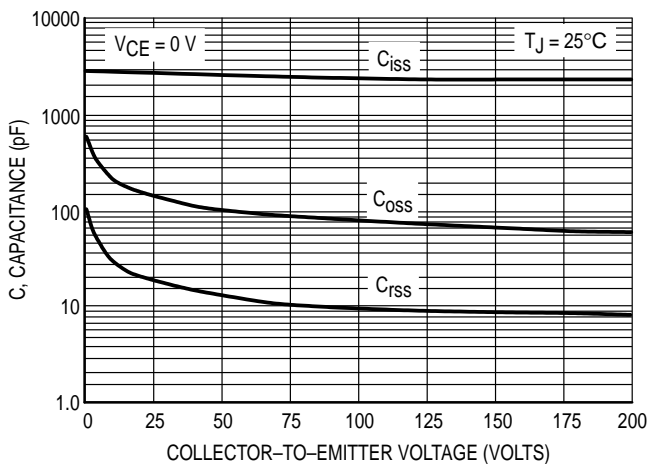


Figure 5. Capacitance Variation

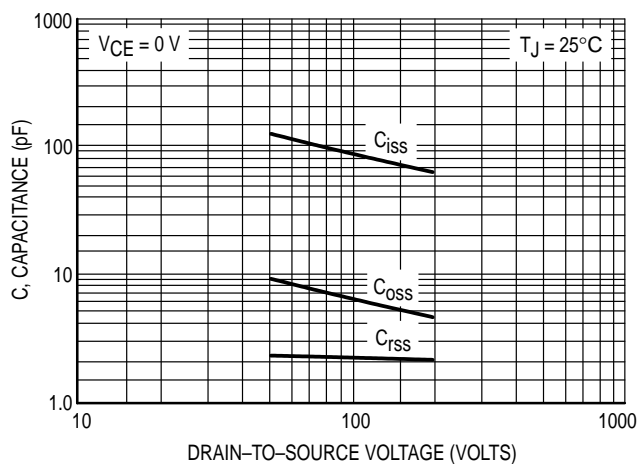


Figure 6. High Voltage Capacitance Variation

MGP20N35CL

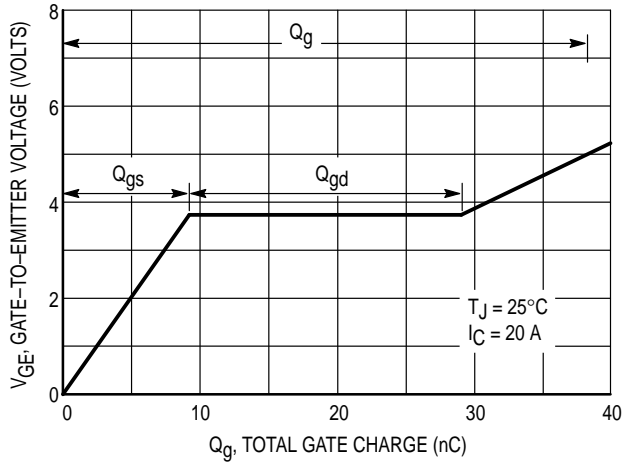


Figure 7. Gate-to-Emitter and Collector-to-Emitter Voltage vs Total Charge

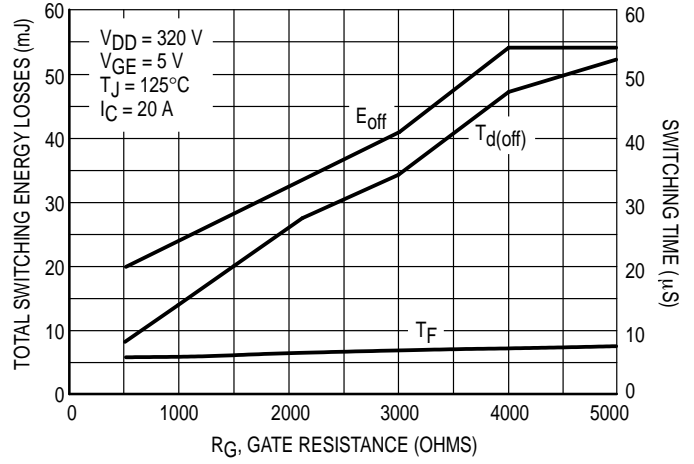


Figure 8. Total Switching Losses versus Gate Temperature

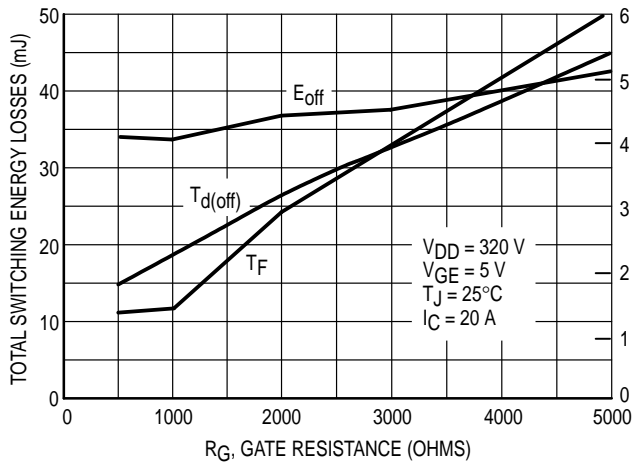


Figure 9. Total Switching Losses versus Gate Resistance

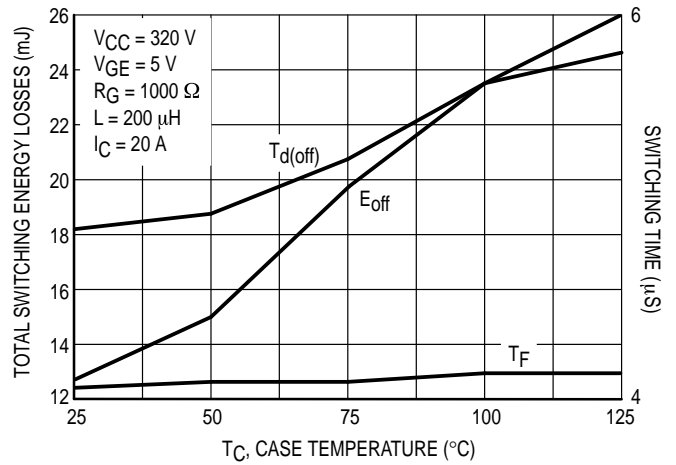


Figure 10. Total Switching Losses versus Case Temperature

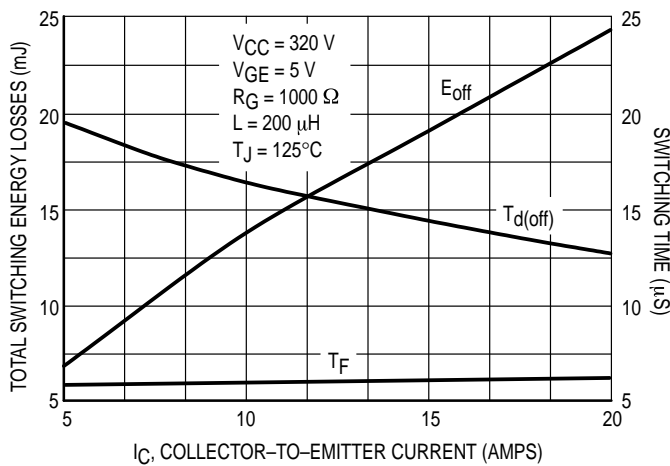


Figure 11. Total Switching Losses versus Collector Current

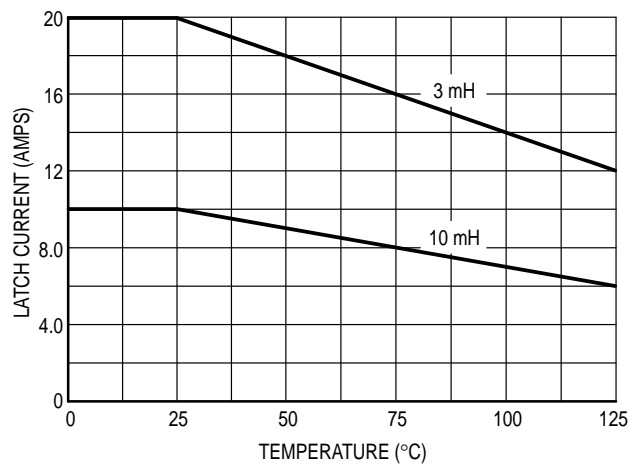


Figure 12. Latch Current versus Temperature

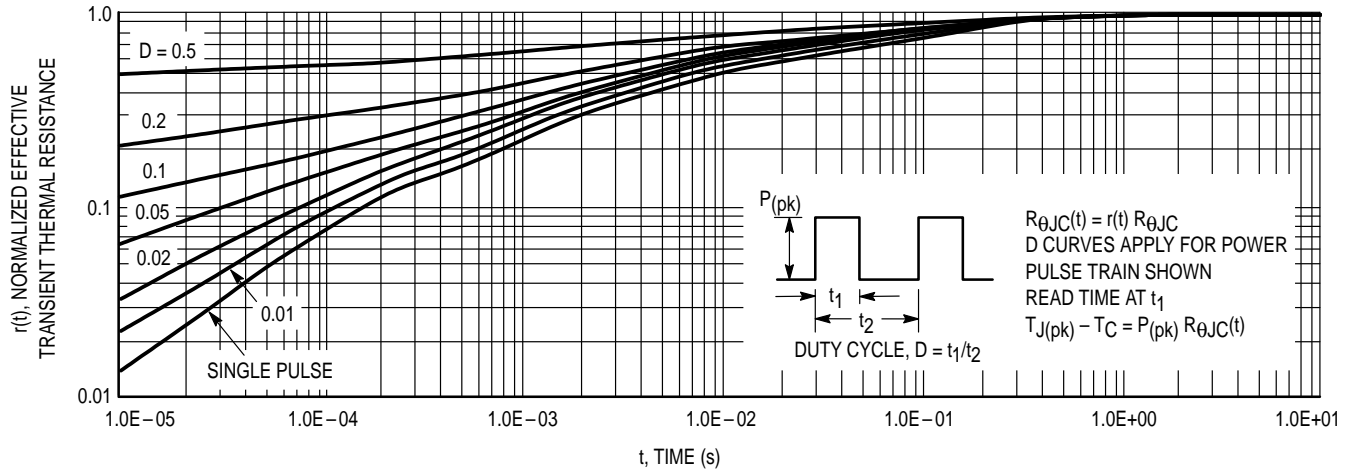
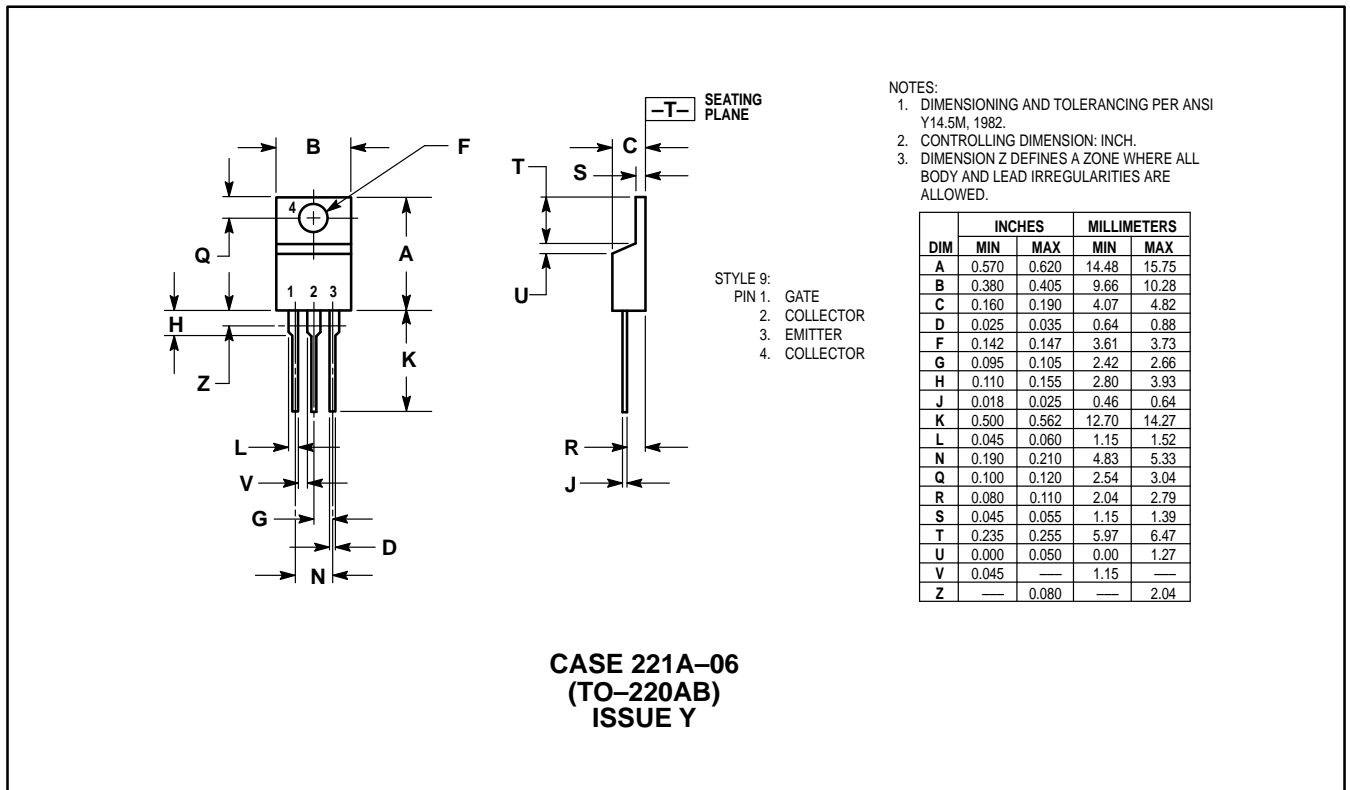



Figure 13. Thermal Response

PACKAGE DIMENSIONS



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